

TECHNICAL DATA SHEET

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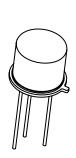
# NPN POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/544

DEVICES			LEVELS
	2N5152	2N5154	JAN
	2N5152L	2N5154L	JANTX
	2N5152U3	2N5154U3	JANTXV
			JANS

### **ABSOLUTE MAXIMUM RATINGS** ( $T_c = +25^{\circ}C$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	100	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.5	Vdc
Collector Current	I <sub>C</sub>	2.0	Adc
Total Power Dissipation <sup>(1)</sup> @ $T_A = +25^{\circ}C$ @ $T_C = +25^{\circ}C$	P <sub>T</sub>	1.0 10	W
Operating & Storage Junction Temperature Range	$T_J$ , $T_{stg}$	-65 to +200	°C
Thermal Resistance, Junction-to Case <sup>(1)</sup>	$R_{\theta JC}$	10 1.7 (U3)	°C/W



#### TO-5 2N5152L, 2N5154L

Note:

1) See 19500/544 for thermal derating curves.

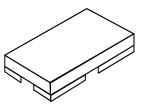
2) This value applies for  $P_W \le 8.3$ ms, duty cycle  $\le 1\%$ .

### ELECTRICAL CHARACTERISTICS ( $T_A = +25^{\circ}C$ , unless otherwise noted)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
OFF CHARACTERTICS					
Collector-Emitter Breakdown Voltage $I_C = 100$ mAdc, $I_B = 0$		V <sub>(BR)CEO</sub>	80		Vdc
$ \begin{array}{l} \mbox{Emitter-Base Cutoff Current} \\ V_{EB} = 4.0 \mbox{Vdc}, \ I_C = 0 \\ V_{EB} = 5.5 \mbox{Vdc}, \ I_C = 0 \end{array} $		I <sub>EBO</sub>		1.0 1.0	µAdc mAdc
Collector-Emitter Cutoff Current $V_{CE} = 60Vdc, V_{BE} = 0$ $V_{CE} = 100Vdc, V_{BE} = 0$		I <sub>CES</sub>		1.0 1.0	µAdc mAdc
Collector-Emitter Cutoff Current $V_{CE} = 40$ Vdc, $I_B = 0$		I <sub>CEO</sub>		50	μAdc
ON CHARACTERTICS					
Forward-Current Transfer Ratio $I_C = 50$ mAdc, $V_{CE} = 5$ Vdc $I_C = 2.5$ Adc, $V_{CE} = 5$ Vdc	2N5152 2N5154 2N5152 2N5154	$\mathbf{h}_{\mathrm{FE}}$	20 50 30 70	 90 200	



2N5152, 2N5154



U-3 2N5152U3, 2N5154U3



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Qualified per MIL-PRF-19500/544

## ELECTRICAL CHARACTERISTICS (con't)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
$I_{\rm C} = 5 {\rm Adc},  V_{\rm CE} = 5 {\rm Vdc}$	2N5152 2N5154	h <sub>FE</sub>	20 40		
Collector-Emitter Saturation Voltage					
$I_{C} = 2.5 \text{Adc}, I_{B} = 250 \text{mAdc}$ $I_{C} = 5.0 \text{Adc}, I_{B} = 500 \text{mAdc}$		V <sub>CE(sat)</sub>		0.75 1.5	Vdc
Base-Emitter Voltage Non-Saturation $I_C = 2.5 Adc$ , $V_{CE} = 5 Vdc$		V <sub>BE</sub>		1.45	Vdc
Base-Emitter Saturation Voltage $I_C = 2.5$ Adc, $I_B = 250$ mAdc $I_C = 5.0$ Adc, $I_B = 500$ mAdc		V <sub>BE(sat)</sub>		1.45 2.2	Vdc

#### **DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions   Magnitude of Common Emitter Small-Signal Short-Circuit   Forward Current Transfer Ratio		Symbol	Min.	Max.	Unit
$I_C = 500$ mAdc, $V_{CE} = 5$ Vdc, $f = 10$ MHz	2N5152 2N5154	$ \mathbf{h}_{\mathrm{fe}} $	6 7		
Small-signal short Circuit Forward-Current Transfer Ratio					
$I_C = 100$ mAdc, $V_{CE} = 5$ Vdc, $f = 1$ KHz	2N5152 2N5154	$\mathbf{h}_{\mathrm{fe}}$	20 50		
Output Capacitance $V_{CB} = 10Vdc, I_E = 0, f = 1.0MHz$		C <sub>obo</sub>		250	pF

## SWITCHING CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Turn-On Time $I_C = 5Adc, I_{B1} = 500mAdc$		t <sub>on</sub>		0.5	μs
Turn-Off Time $R_L = 6\Omega$		t <sub>off</sub>		1.5	μs
Storage Time	$I_{B2} = -500 \text{mAdc}$	t <sub>s</sub>		1.4	μs
Fall Time	$V_{BE(OFF)} = 3.7Vdc$	t <sub>f</sub>		0.5	μs

#### SAFE OPERATING AREA

 $\label{eq:2.1} \begin{array}{l} \textbf{DC Tests} \\ T_{C} = +25^{\circ}\text{C}, \ 1 \ \text{Cycle}, \ t_{P} = 1.0\text{s} \\ \hline \textbf{Test 1} \\ V_{CE} = 5.0 \ \text{Vdc}, \ I_{C} = 2.0 \ \text{Adc} \\ \hline \textbf{Test 2} \\ V_{CE} = 32 \ \text{Vdc}, \ I_{C} = 310 \ \text{mAdc} \\ \hline \textbf{Test 3} \\ V_{CE} = 80 \ \text{Vdc}, \ I_{C} = 12.5 \ \text{mAdc} \end{array}$ 

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